

Transport properties of Fe/Si multilayers with various iron thickness

P. Wandziuk and T. Luciński

*Institute of Molecular Physics, Polish Academy of Sciences
M. Smoluchowskiego 17, 60-179 Poznań, Poland*

Antiferromagnetically coupled Fe/Si multilayers attract a lot of attention due to their potential application in spintronics. In order to characterize the Fe/Si interfaces and their influence on interlayer exchange coupling we follow the evolution of transport and magnetic properties, which are related to formation of interfacial Fe-Si phases in particular stages of the multilayer growth. In this work $[\text{Fe}(d_{\text{Fe}})/\text{Si}(1.1 \text{ nm})]_{15}$ multilayers, for iron thickness $0.25 < d_{\text{Fe}} < 4 \text{ nm}$, deposited by magnetron sputtering, have been studied. Silicon layer thickness is chosen to correspond to maximum of antiferromagnetic coupling between Fe layers, as reported previously [1]. Transport properties are investigated by Hall effect, resistance, and magnetoresistance measurements. A transition from semiconducting to metallic behavior occurs for Fe thickness between 0.7 and 1 nm. Both magnetic moment measurements and the $4\pi M_s$ data extracted from anomalous Hall effect show that samples lose their magnetic moment for $d_{\text{Fe}} < 0.5 \text{ nm}$. Temperature coefficient of resistance (TCR) and $4\pi M_s$ dependence on Fe thickness, taken at 250 K, is shown in Figure 1. In the range $0.5 < d_{\text{Fe}} < 1 \text{ nm}$ the investigated multilayers possess both semiconducting and magnetic properties. Based on the resistivity data of whole stack and individual components we make efforts to estimate the interfacial Fe-Si mixture contribution to resistivity of investigated multilayers.

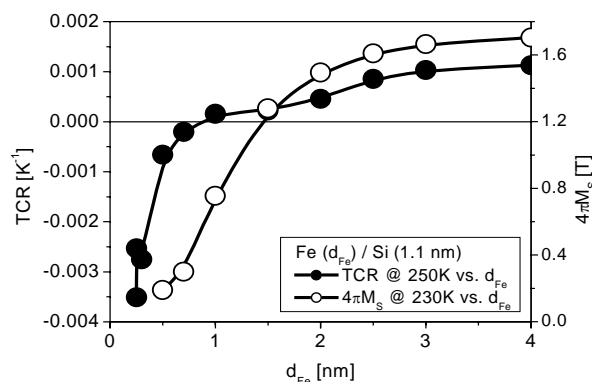


Fig. 1. Temperature coefficient of resistance (TCR) of Fe/Si multilayers, and $4\pi M_s$ data as a function of Fe thickness (d_{Fe}).

[1] T. Luciński, P. Wandziuk, J. Baszyński, B. Szymański, F. Stobiecki, J. Zweck, phys. stat. sol. (c) **3** (2006) 93.

Name of the presenting author (poster): Piotr Wandziuk
e-mail address: wandziuk@ifmpan.poznan.pl
url's: <http://www.ifmpan.poznan.pl>